

BUK6C2R1-55C

N-channel TrenchMOS intermediate level FET Rev. 3 — 18 January 2012

Product data sheet

1. **Product profile**

1.1 General description

Intermediate level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in high-performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant
- High current handling capability, up to 320 A
- Low conduction losses due to very low on-state resistance
- Suitable for standard and logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoids
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

1.4 Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-------------------|----------------------------------|---|-----|-----|-----|------|
| V_{DS} | drain-source voltage | $T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$ | - | - | 55 | V |
| I _D | drain current | $V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C};$ see Figure 1 | - | - | 228 | Α |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; see <u>Figure 2</u> | - | - | 300 | W |
| Static chara | acteristics | | | | | |
| R _{DSon} | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 90 \text{ A};$ $T_j = 25 \text{ °C};$ see Figure 11 | - | 1.9 | 2.3 | mΩ |



Table 1. Quick reference data ...continued

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|--|--|-----|-----|-----|------|
| Dynamic c | haracteristics | | | | | |
| Q_{GD} | gate-drain charge | I_D = 180 A; V_{DS} = 44 V; V_{GS} = 10 V; see <u>Figure 13</u> ; see <u>Figure 14</u> | - | 79 | - | nC |
| Avalanche ruggedness | | | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | $I_D = 120 \text{ A}; V_{sup} \le 55 \text{ V};$ $R_{GS} = 50 \Omega; V_{GS} = 10 \text{ V};$ $T_{j(init)} = 25 ^{\circ}\text{C}; \text{ unclamped}$ | - | - | 770 | mJ |

2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|--|----------------|
| 1 | G | gate | | |
| 2 | S | source | mb | D |
| 3 | S | source | | |
| 4 | D | drain[1] | ii | |
| 5 | S | source | —————————————————————————————————————— | mbb076 S |
| 6 | S | source | | |
| 7 | S | source | SOT427 (D2PAK) | |
| mb | D | mounting base; connected to drain | | |

^[1] It is not possible to connect to pin 4 of the SOT427 package.

3. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|--------------|---------|--|---------|
| | Name | Description | Version |
| BUK6C2R1-55C | D2PAK | plastic single-ended surface-mounted package (D2PAK); 7 leads (one lead cropped) | SOT427 |

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|----------------------|--|---|----------------|-----|------|
| V_{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | - | 55 | V |
| V_{GS} | gate-source voltage | Pulsed | <u>[1]</u> -20 | 20 | V |
| | | DC | <u>[2]</u> -16 | 16 | V |
| I _D | drain current | T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u> | - | 228 | Α |
| | | T_{amb} = 100 °C; V_{GS} = 10 V; see <u>Figure 1</u> | - | 162 | Α |
| I _{DM} | peak drain current | T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; see Figure 3 | - | 914 | Α |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; see <u>Figure 2</u> | - | 300 | W |
| T _{stg} | storage temperature | | -55 | 175 | °C |
| Tj | junction temperature | | -55 | 175 | °C |
| Source-drain | diode | | | | |
| Is | source current | T _{mb} = 25 °C | - | 228 | Α |
| I _{SM} | peak source current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$ | - | 914 | Α |
| Avalanche ru | iggedness | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | I_D = 120 A; $V_{sup} \le 55$ V; $R_{GS} = 50$ Ω; $V_{GS} = 10$ V; $T_{j(init)} = 25$ °C; unclamped | - | 770 | mJ |

- [1] Accumulated pulse duration not to exceed 5mins.
- [2] -16V accumulated duration not to exceed 168 hrs.

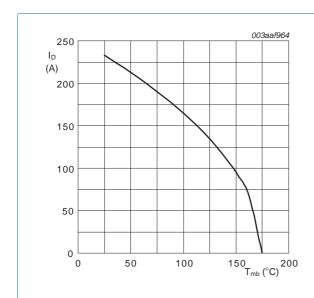
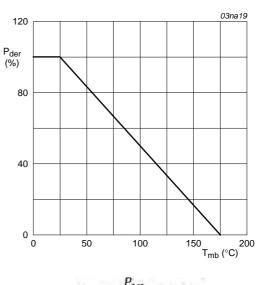


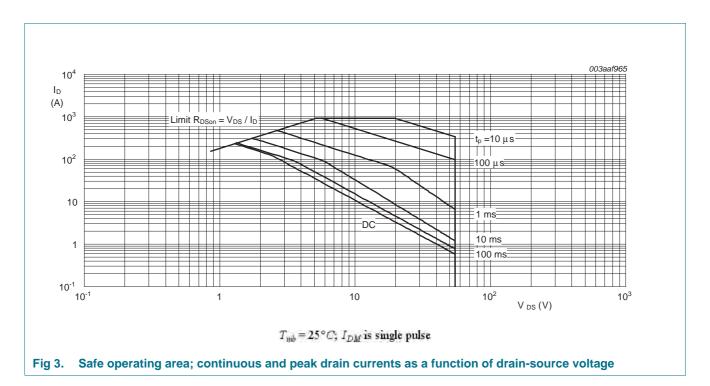
Fig 1. Continuous drain current as a function of mounting base temperature



 $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$

Fig 2. Normalized total power dissipation as a function of mounting base temperature

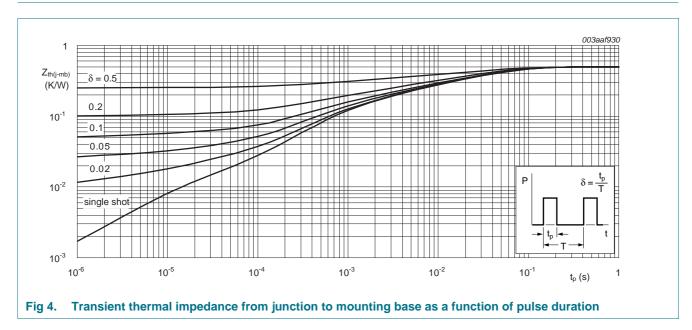
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5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------|---|--------------|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | see Figure 4 | - | - | 0.5 | K/W |



6. Characteristics

Table 6. Characteristics

| Table 6. | Characteristics | | | | | |
|--|----------------------------------|---|-----|-------|-------|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| Static cha | aracteristics | | | | | |
| $V_{(BR)DSS}$ | drain-source | $I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ | 55 | - | - | V |
| | breakdown voltage | $I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$ | 50 | - | - | V |
| $V_{GS(th)}$ | gate-source threshold voltage | $I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ °C}$; see <u>Figure 9</u> ; see <u>Figure 10</u> | 1.8 | 2.3 | 2.8 | V |
| V_{GSth} | gate-source threshold voltage | I_D = 2.5 mA; V_{DS} = V_{GS} ; T_j = 175 °C; see <u>Figure 10</u> | 8.0 | - | - | V |
| | | I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; see <u>Figure 10</u> | - | - | 3.3 | V |
| I _{DSS} | drain leakage current | $V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | 0.04 | 1 | μΑ |
| | | $V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 ^{\circ}\text{C}$ | - | - | 500 | μΑ |
| I _{GSS} | gate leakage current | $V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | - | 2 | 100 | nΑ |
| | | $V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | 2 | 100 | nΑ |
| R _{DSon} drain-source o resistance | drain-source on-state resistance | V_{GS} = 10 V; I_{D} = 90 A; T_{j} = 25 °C; see <u>Figure 11</u> | - | 1.9 | 2.3 | mΩ |
| | | $V_{GS} = 5 \text{ V}; I_D = 90 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 11</u> | - | 2.4 | 3.1 | mΩ |
| | | $V_{GS} = 4.5 \text{ V}; I_D = 90 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 11 | - | 2.6 | 3.7 | mΩ |
| | | V_{GS} 10 V; I_D = 90 A; T_j = 175 °C; see <u>Figure 11</u> ; see <u>Figure 12</u> | - | - | 5.7 | mΩ |
| Dynamic | characteristics | | | | | |
| Q _{G(tot)} | total gate charge | I_D = 180 A; V_{DS} = 44 V; V_{GS} = 10 V; see <u>Figure 13</u> ; see <u>Figure 14</u> | - | 253 | - | nC |
| | | I_D = 180 A; V_{DS} = 44 V; V_{GS} = 5 V; see <u>Figure 13</u> ; see <u>Figure 14</u> | - | 140 | - | nC |
| Q _{GS} | gate-source charge | $I_D = 180 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 10 \text{ V};$ | - | 40 | - | nC |
| Q_{GD} | gate-drain charge | see Figure 13; see Figure 14 | - | 79 | - | nC |
| C _{iss} | input capacitance | $V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ | - | 12000 | 16000 | pF |
| C _{oss} | output capacitance | T _j = 25 °C; see <u>Figure 15</u> | - | 1075 | 1290 | pF |
| C _{rss} | reverse transfer capacitance | | - | 730 | 1000 | pF |
| t _{d(on)} | turn-on delay time | $V_{DS} = 30 \text{ V}; R_L = 0.3 \Omega; V_{GS} = 10 \text{ V};$ | - | 43 | - | ns |
| t _r | rise time | $R_{G(ext)} = 10 \Omega$ | - | 206 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 412 | - | ns |
| t _f | fall time | | - | 190 | - | ns |
| Source-d | rain diode | | | | | |
| V _{SD} | source-drain voltage | $I_S = 80 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 16</u> | - | 0.8 | 1.2 | V |
| t _{rr} | reverse recovery time | $I_S = 50 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$; | - | 56 | - | ns |
| Q _r | recovered charge | $V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$ | - | 115 | - | nC |

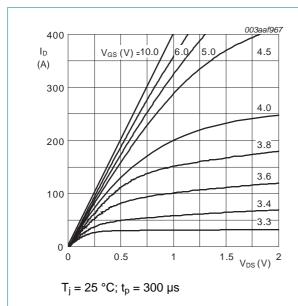


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

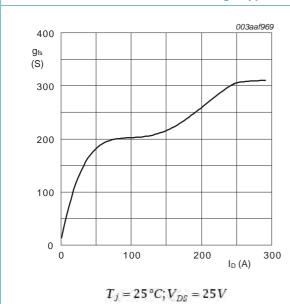


Fig 7. Forward transconductance as a function of drain current; typical values

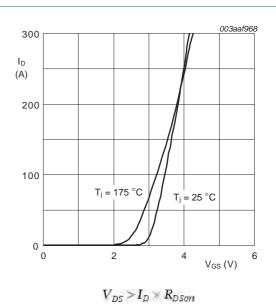


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

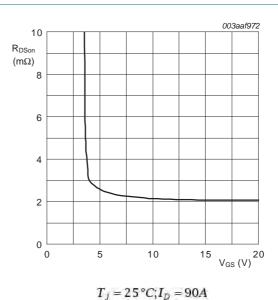


Fig 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

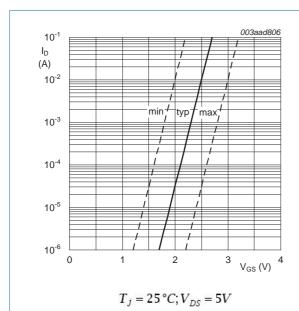


Fig 9. Sub-threshold drain current as a function of gate-source voltage

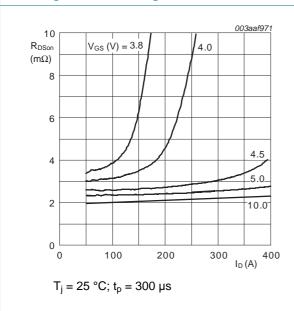


Fig 11. Drain-source on-state resistance as a function of drain current; typical values

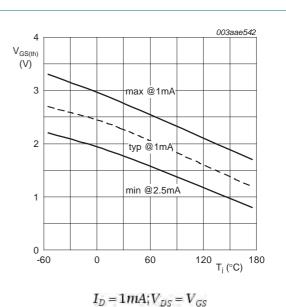


Fig 10. Gate-source threshold voltage as a function of junction temperature

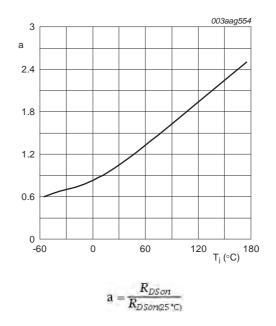
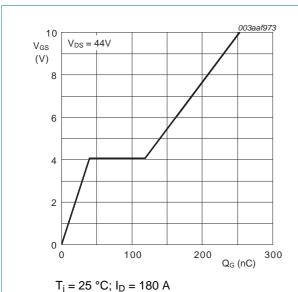


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature



1j = 25 0, 1g = 100 A

Fig 13. Gate-source voltage as a function of gate charge; typical values

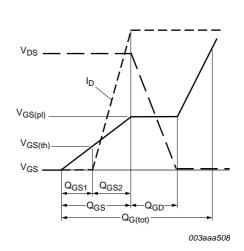
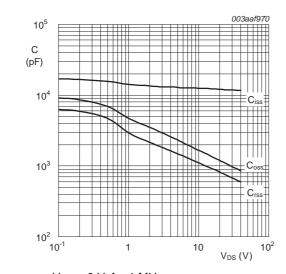
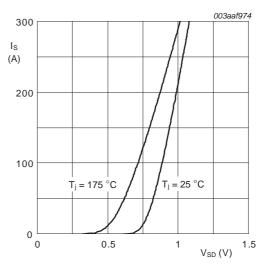


Fig 14. Gate charge waveform definitions



 $V_{GS} = 0 V; f = 1 MHz$

Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



 $V_{GS} = 0 V$

Fig 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

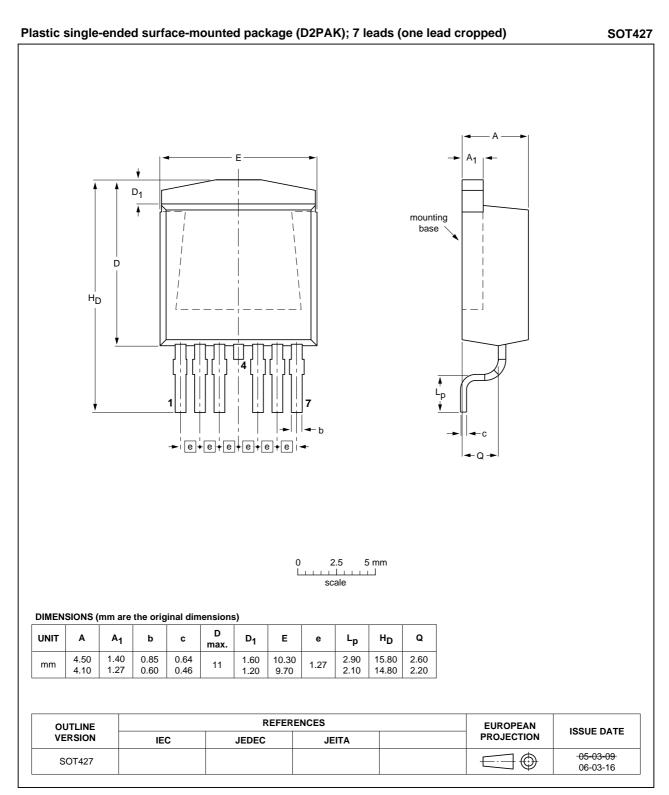


Fig 17. Package outline SOT427 (D2PAK)

8. Revision history

Table 7. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|------------------|-----------------------------------|-------------------------------|---------------|------------------|
| BUK6C2R1-55C v.3 | 20120118 | Product data sheet | - | BUK6C2R1-55C v.2 |
| Modifications: | Status change | ed from preliminary to produc | et. | |
| BUK6C2R1-55C v.2 | 20111221 | Preliminary data shee | t - | BUK6C2R1-55C v.1 |

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9.1 Data sheet status

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Nexperia

N-channel TrenchMOS intermediate level FET

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